Product data sheet

1. General description

Ultrafast power diode in a SOD113 (2-lead TO-220F) plastic package.

2. Features and benefits

- Fast switching
- Low forward voltage drop
- Soft recovery characteristic

3. Applications

- Discontinuous Current Mode (DCM) Power Factor Correction (PFC)
- · High frequency switched-mode power supplies
- TV power supplies

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_R	reverse voltage	DC		-	-	800	V
I _{F(AV)}	average forward current	$\delta = 0.5 \; ; T_h \le 88 ^{\circ}\text{C}; \text{SQW}; \underline{\text{Fig. 1}}; \\ \underline{\text{Fig. 2}}; \underline{\text{Fig. 3}}$		-	-	8	Α
I _{FRM}	repetitive peak forward current	$\delta = 0.5 \; ; t_p = 25 \; \mu s; T_h \le 88 \; ^{\circ}C; \; SQW$		-	-	16	Α
I _{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; SIN; <u>Fig. 4</u>		-	-	80	Α
		t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; SIN; <u>Fig. 4</u>		-	-	88	Α
Static characte	eristics						
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 6</u>		-	1.4	1.7	V
		I _F = 8 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.2	1.5	V
Dynamic characteristics							
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}; V_R = 30 \text{ V}; dI_F/dt = 100 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$		-	40	55	ns

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	K — A
2	Α	anode		001aaa020
mb	n.c.	mounting base; isolated	TO-220F (SOD113)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BYR29X-800P	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113			

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	800	V
V_{RWM}	crest working reverse voltage		-	800	V
V_R	reverse voltage	DC	-	800	V
I _{F(AV)}	average forward current	δ = 0.5 ; T _h \leq 88 °C; SQW; <u>Fig. 1</u> ; <u>Fig. 2</u> ; <u>Fig. 3</u>	-	8	Α
I _{FRM}	repetitive peak forward current	$\delta = 0.5 \; ; t_p = 25 \; \mu s; T_h \le 88 \; ^{\circ}C; \; SQW$	-	16	Α
I _{FSM}	non-repetitive peak	t_p = 10 ms; $T_{j(init)}$ = 25 °C; SIN; Fig. 4	-	80	Α
	forward current	t_p = 8.3 ms; $T_{j(init)}$ = 25 °C; SIN; Fig. 4	-	88	Α
T _{stg}	storage temperature		-40	175	°C
T _j	junction temperature		-	175	°C

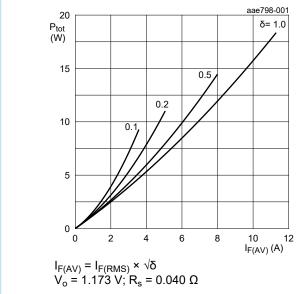


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

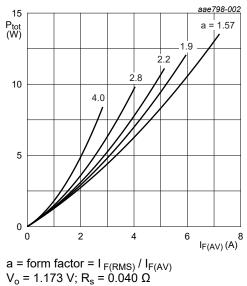


Fig. 2. Forward power dissipation as a function of average forward current; sinusoidal waveform;

maximum values

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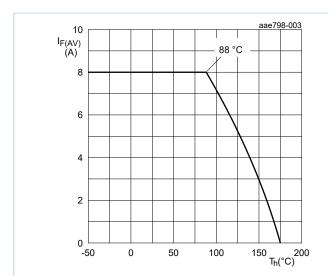


Fig. 3. Forward current as a function of heatsink temperature; maximum values

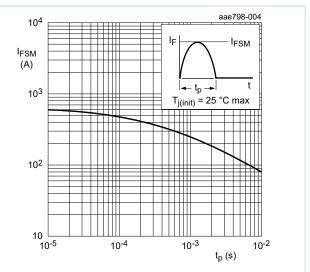


Fig. 4. Non-repetitive peak forward current as a function of pulse width; sinusoidal waveform; maximum values

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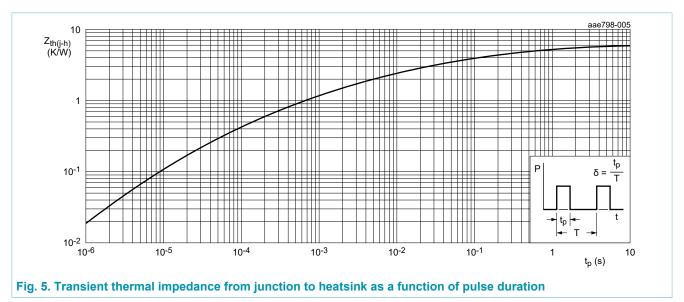
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8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance from junction to heatsink	with heatsink compound; Fig. 5	-	-	6	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	60	-	K/W



9. Isolation characteristics

Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	50 Hz ≤ f ≤ 60 Hz; RH ≤ 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	from cathode to external heatsink	-	10	-	pF

10. Characteristics

Table 7. Characteristics

from cathode to external heatsink

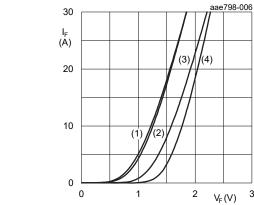
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Static characteristics								
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; <u>Fig. 6</u>		-	1.4	1.7	V	
		I _F = 8 A; T _j = 150 °C; <u>Fig. 6</u>		-	1.2	1.5	V	
I _R	reverse current	V _R = 800 V; T _j = 25 °C		-	-	10	μA	
		V _R = 800 V; T _j = 150 °C		-	-	0.2	mA	
Dynamic ch	naracteristics						,	
t _{rr}	reverse recovery time	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$; Fig. 7		-	40	55	ns	
I _{RM}	peak reverse recovery current	$I_F = 1 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 100 \text{ A/}\mu\text{s}$; $T_j = 25 \text{ °C}$		-	-	5	Α	
Q _r	recovered charge	$I_F = 2 \text{ A}$; $V_R = 30 \text{ V}$; $dI_F/dt = 20 \text{ A/s}$; $T_j = 25 \text{ °C}$		-	60	110	nC	

 dI_F

dt

 I_{RM}

 I_{R}



 V_o = 1.173 V; R_s = 0.040 Ω (1) T_j = 175 °C; typical values (2) T_j = 150 °C; typical values (3) T_j = 175 °C; maximum values (4) T_j = 25 °C; maximum values



Fig. 7. Reverse recovery definitions; ramp recovery



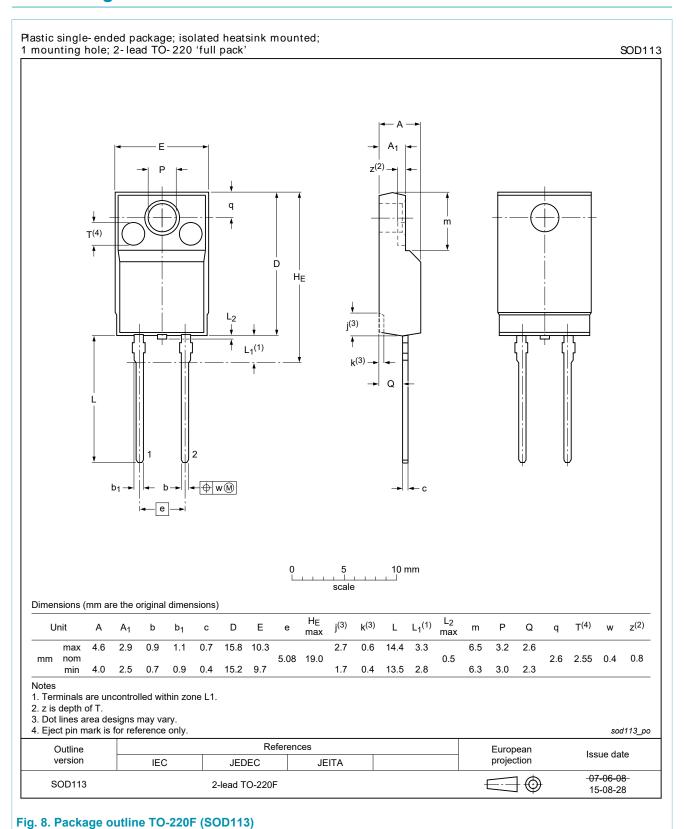
time

003aac562

100 %

25 %

11. Package outline



12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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